

Silicon Diffused Power Transistor

BU2508AF

GENERAL DESCRIPTION

Enhanced performance, new generation, high-voltage, high-speed switching npn transistor in a plastic full-pack envelope intended for use in horizontal deflection circuits of colour television receivers. Features exceptional tolerance to base drive and collector current load variations resulting in a very low worst case dissipation.

QUICK REFERENCE DATA

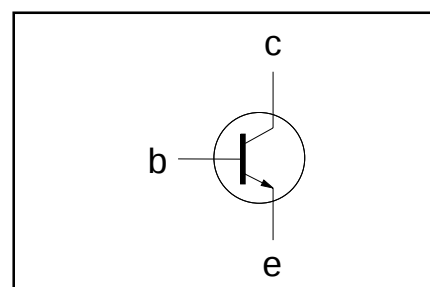
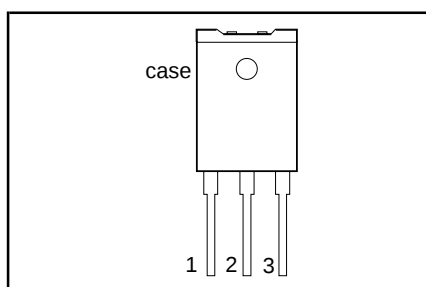
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25\text{ }^{\circ}\text{C}$	-	45	W
V_{CESat}	Collector-emitter saturation voltage	$I_C = 4.5\text{ A}; I_B = 1.1\text{ A}$	-	1	V
I_{Csat}	Collector saturation current		4.5	-	A
t_f	Fall time	$I_{Csat} = 4.5\text{ A}; I_{B(end)} = 1.1\text{ A}$	0.4	0.6	μs

PINNING - SOT199

PIN CONFIGURATION

SYMBOL

PIN	DESCRIPTION
1	base
2	collector
3	emitter
case	isolated



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
I_B	Base current (DC)		-	4	A
I_{BM}	Base current peak value		-	6	A
$-I_{B(AV)}$	Reverse base current	average over any 20 ms period	-	100	mA
$-I_{BM}$	Reverse base current peak value ¹		-	5	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25\text{ }^{\circ}\text{C}$	-	45	W
T_{stg}	Storage temperature		-65	150	$^{\circ}\text{C}$
T_j	Junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Junction to heatsink	without heatsink compound	-	3.7	K/W
$R_{th\ j-hs}$	Junction to heatsink	with heatsink compound	-	2.8	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	35	-	K/W

¹ Turn-off current.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. $\leq 65\%$; clean and dustfree	-		2500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	22	-	pF

STATIC CHARACTERISTICS

 $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current ²	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	-	-	1.0	mA
I_{CES}		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_J = 125\text{ }^{\circ}\text{C}$	-	-	2.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = 7.5\text{ V}; I_C = 0\text{ A}$	-	-	1.0	mA
BV_{EBO}	Emitter-base breakdown voltage	$I_B = 1\text{ mA}$	7.5	13.5	-	V
$V_{CEOsust}$	Collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 100\text{ mA};$ $L = 25\text{ mH}$	700	-	-	V
V_{CEsat}	Collector-emitter saturation voltages	$I_C = 4.5\text{ A}; I_B = 1.1\text{ A}$	-	-	1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = 4.5\text{ A}; I_B = 1.7\text{ A}$	-	-	1.1	V
h_{FE}	DC current gain	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$	-	13	-	
h_{FE}		$I_C = 4.5\text{ A}; V_{CE} = 1\text{ V}$	4	5.5	7.0	

DYNAMIC CHARACTERISTICS

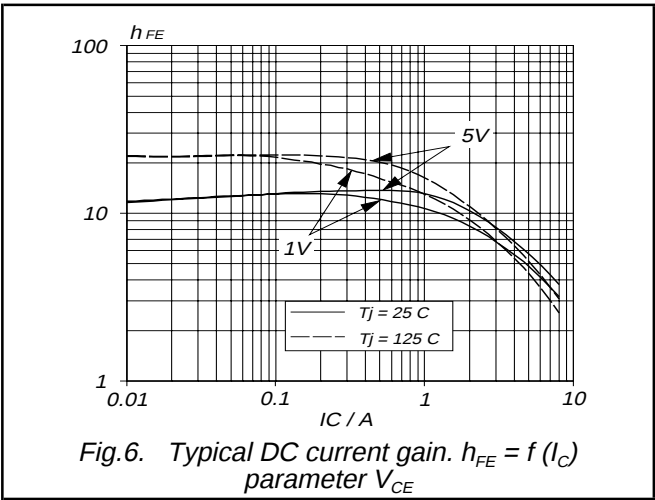
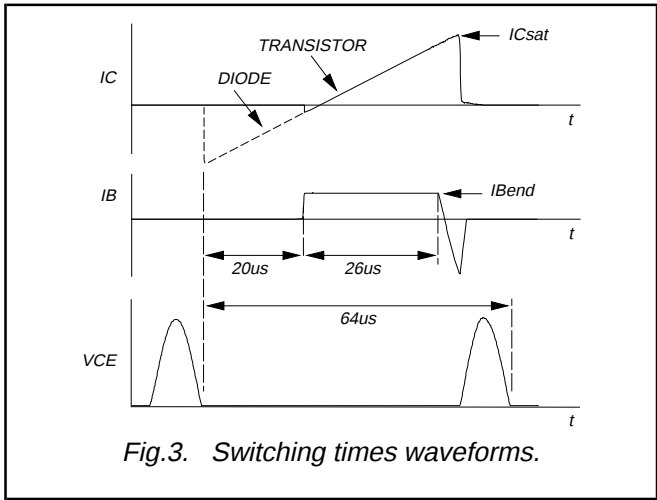
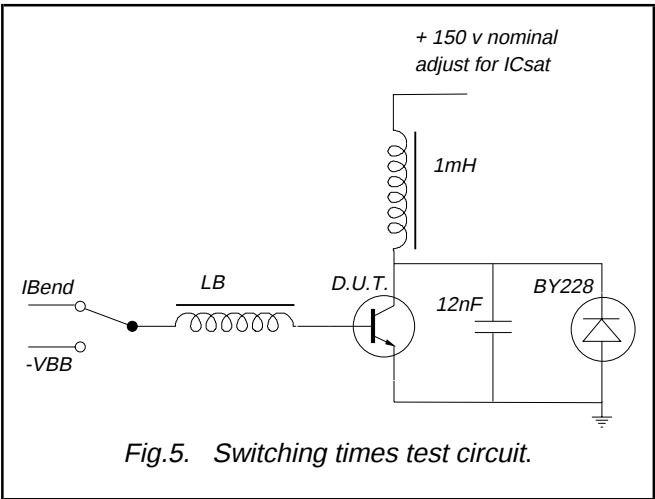
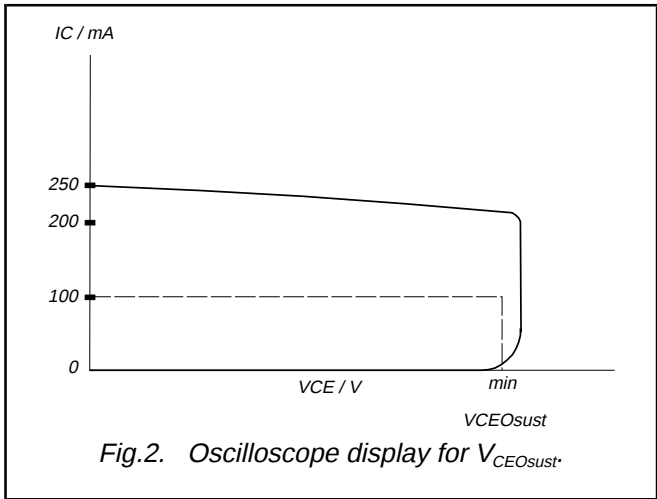
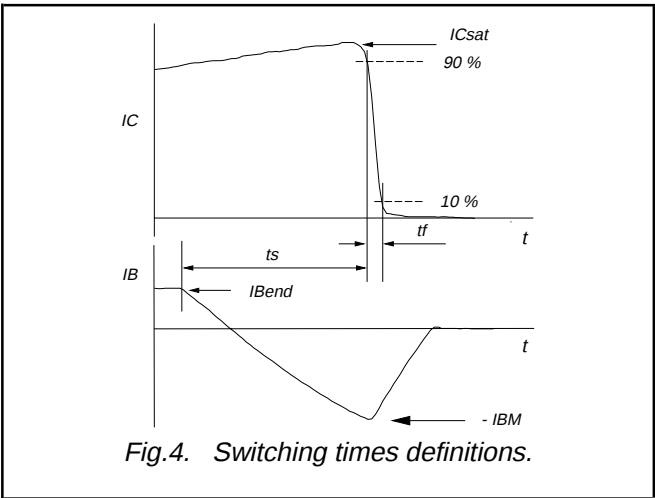
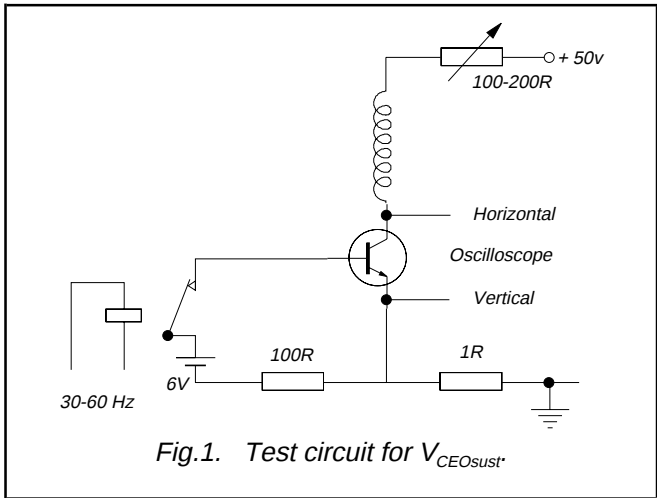
 $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
C_c	Collector capacitance	$I_E = 0\text{ A}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	80	-	pF
t_s t_f	Switching times (16 kHz line deflection circuit)	$I_{Csat} = 4.5\text{ A}; I_{B(end)} = 1.1\text{ A}; L_B = 6\text{ }\mu\text{H};$ $-V_{BB} = 4\text{ V}; (-dI_B/dt = 0.6\text{ A}/\mu\text{s})$	5.0 0.4	6.0 0.6	μs μs
	Turn-off storage time				
t_s t_f	Switching times (38 kHz line deflection circuit)	$I_{Csat} = 4.0\text{ A}; I_{B(end)} = 0.9\text{ A}; L_B = 6\text{ }\mu\text{H};$ $-V_{BB} = 4\text{ V}; (-dI_B/dt = 0.6\text{ A}/\mu\text{s})$	4.7 0.25	5.7 0.35	μs μs
	Turn-off storage time				
t_s t_f	Turn-off storage time				μs μs
	Turn-off fall time				

² Measured with half sine-wave voltage (curve tracer).

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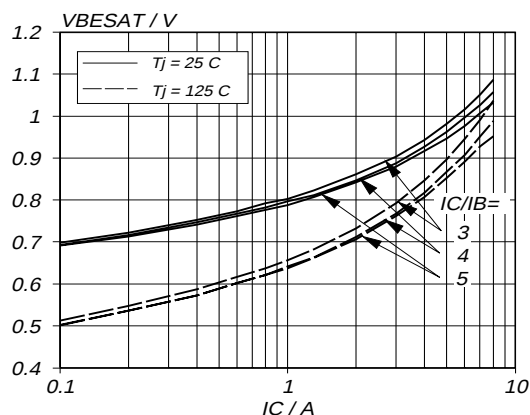


Fig.7. Typical base-emitter saturation voltage.
 $V_{BE(sat)} = f(I_C)$; parameter I_C/I_B

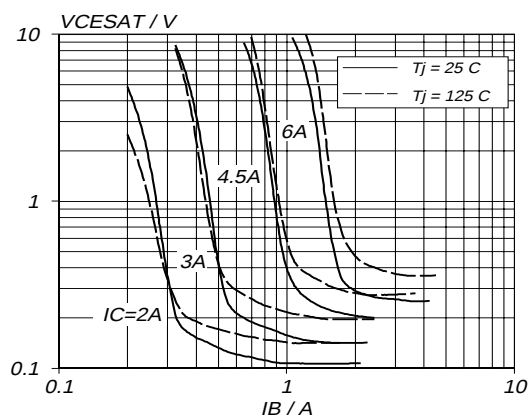


Fig.10. Typical collector-emitter saturation voltage.
 $V_{CE(sat)} = f(I_B)$; parameter I_C

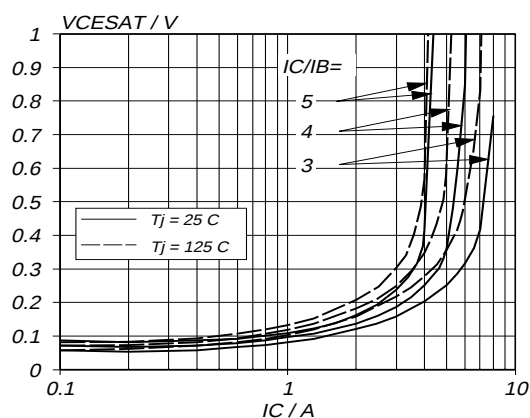


Fig.8. Typical collector-emitter saturation voltage.
 $V_{CE(sat)} = f(I_C)$; parameter I_C/I_B

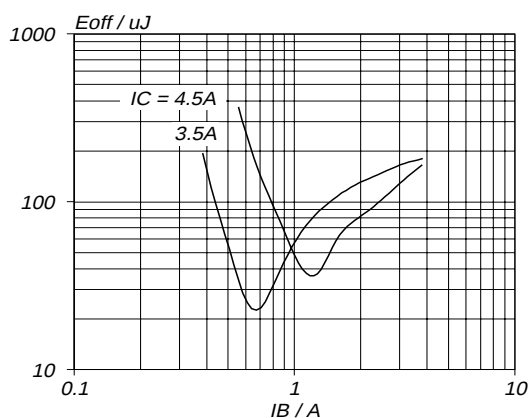


Fig.11. Typical turn-off losses. $T_J = 85^\circ\text{C}$
 $E_{off} = f(I_B)$; parameter I_C ; $f = 16\text{ kHz}$

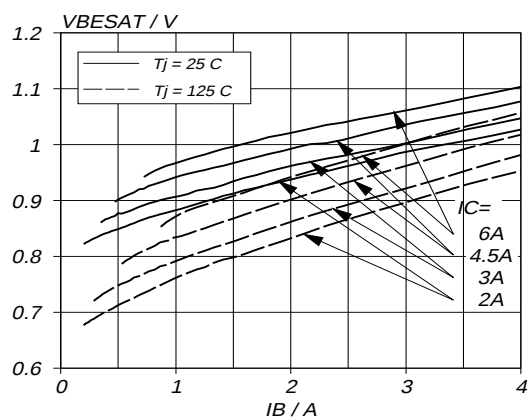


Fig.9. Typical base-emitter saturation voltage.
 $V_{BE(sat)} = f(I_B)$; parameter I_C

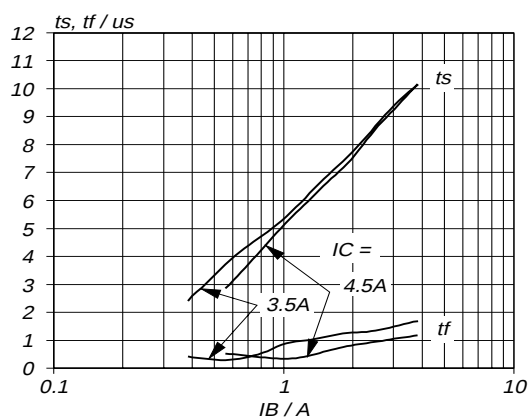


Fig.12. Typical collector storage and fall time.
 $t_s = f(I_B)$; $t_f = f(I_B)$; parameter I_C ; $T_J = 85^\circ\text{C}$; $f = 16\text{ kHz}$

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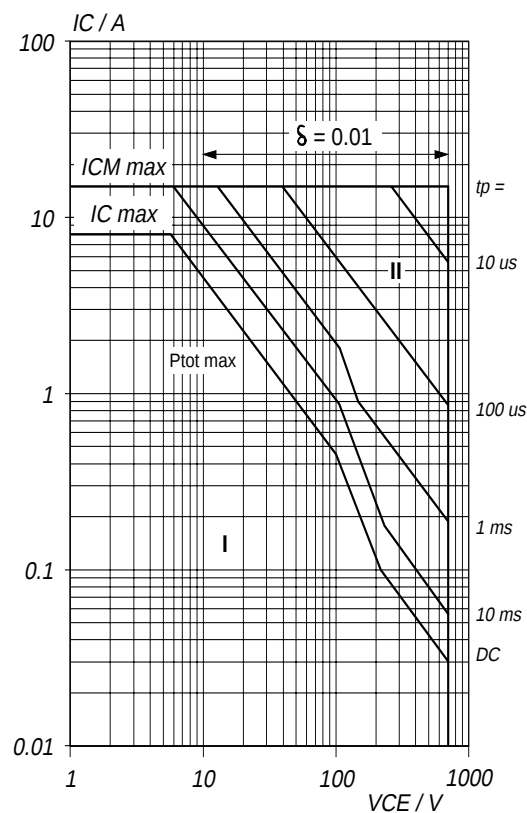


Fig.13. Forward bias safe operating area. $T_{hs} = 25^\circ C$
I Region of permissible DC operation.
II Extension for repetitive pulse operation.

NB: Mounted with heatsink compound and 30 ± 5 newton force on the centre of the envelope.

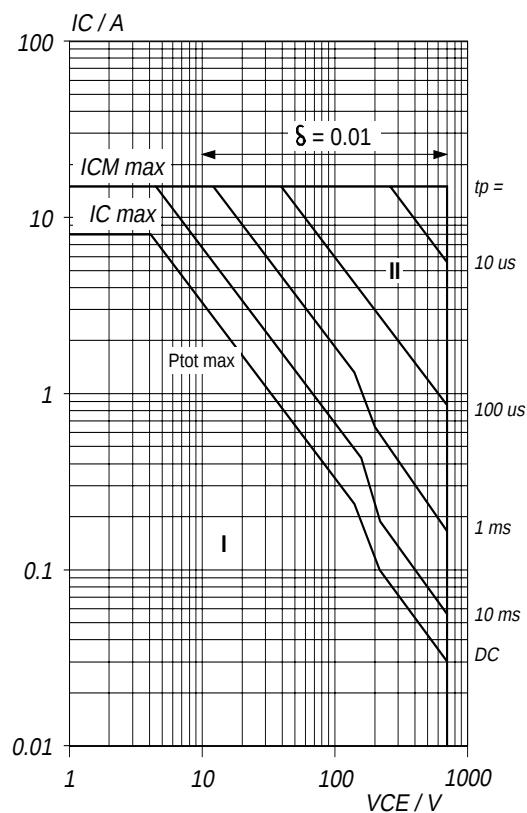


Fig.15. Forward bias safe operating area. $T_{hs} = 25^\circ C$
I Region of permissible DC operation.
II Extension for repetitive pulse operation.

NB: Mounted without heatsink compound and 30 ± 5 newton force on the centre of the envelope.

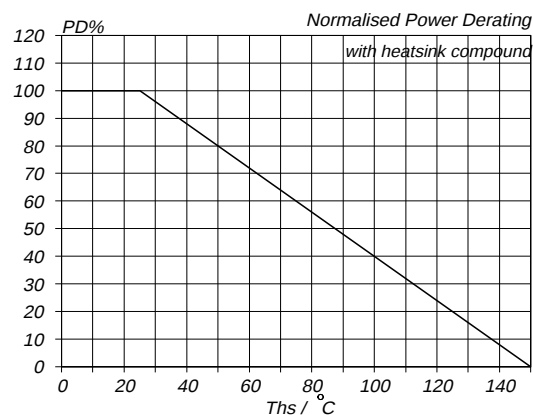
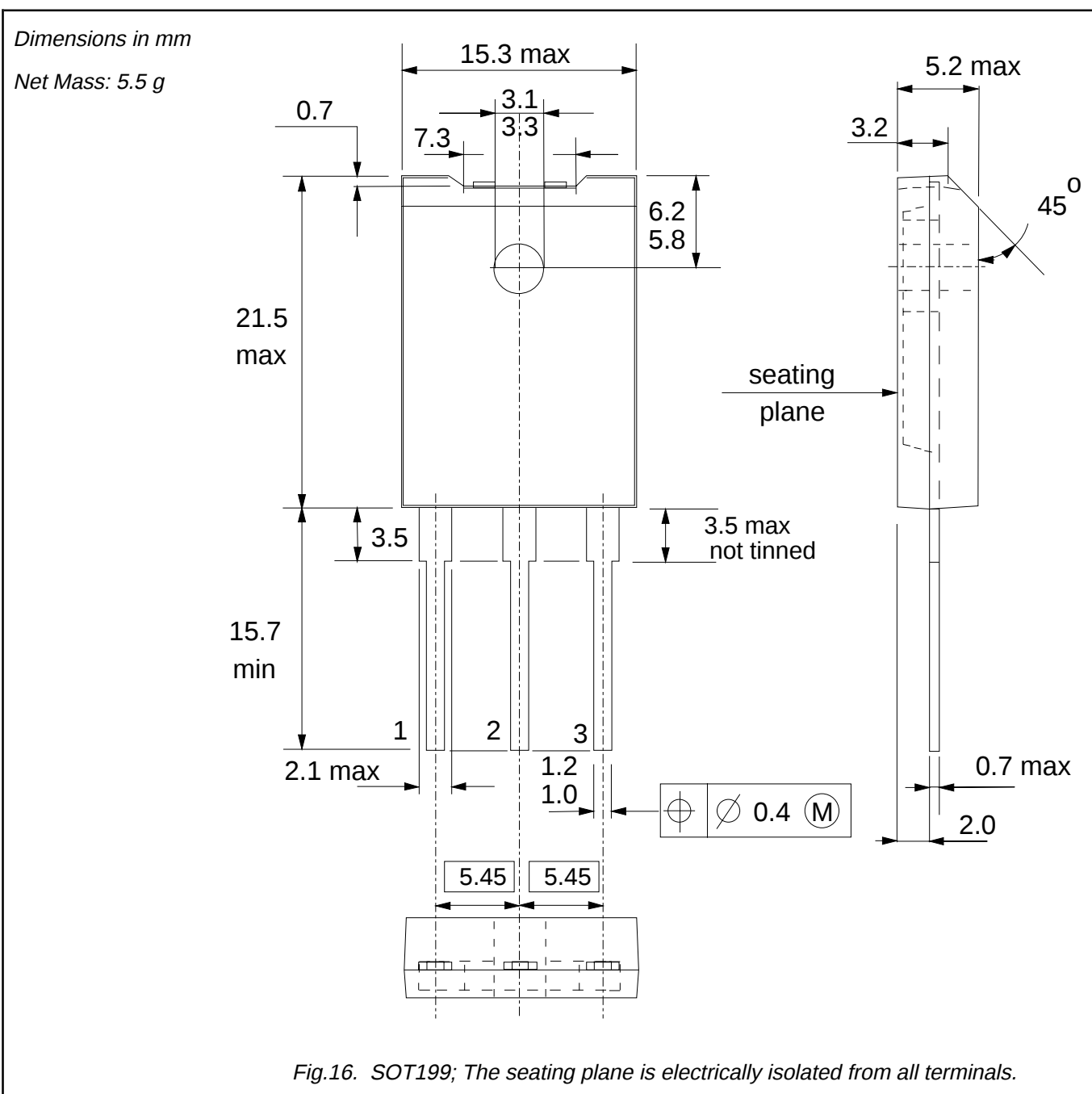


Fig.14. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D 25^\circ C} = f(T_{hs})$

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MECHANICAL DATA



Notes

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".